



1. SiC肖特基二极管器件产品选型表 (Device)

序号	型号	反向电压	平均正向电流	正向压降VF (V)		最高工作结温	总电容电荷	封装
		V _{RRM} (V)	I _F (A)	T _J =25°C	T _J =175°C	T _{Jmax} (P)	(nC)	
1	H3D04065N6	650	4	1.4	1.8	175	9.5	DFN 5*6
2	H3D04065A	650	4	1.4	1.8	175	9.5	TO-220-2L
3	H3D04065E	650	4	1.4	1.8	175	9.5	TO-252-2L
4	H3D06065A	650	6	1.4	1.8	175	17	TO-220-2L
5	H3D06065E	650	6	1.4	1.8	175	17	TO-252-2L
6	H3D08065A	650	8	1.4	1.8	175	22	TO-220-2L
7	H3D08065G	650	8	1.4	1.8	175	22	TO-263
8	H3D10065A	650	10	1.4	1.8	175	28	TO-220-2L
9	H3D10065F	650	10	1.4	1.8	175	28	TO-220F-2L 全封装
10	H3D10065G	650	10	1.4	1.8	175	28	TO-263
11	H3D10065I	650	10	1.4	1.8	175	28	TO-220-2L-内绝缘
12	H3D12065B	650	12	1.4	1.8	175	34	TO-220-3L
13	H3D16065A	650	16	1.4	1.8	175	41	TO-220-2L
14	H3D20065A	650	20	1.4	1.8	175	65	TO-220-2L
15	H3D20065D	650	20	1.4	1.8	175	56	TO-247-3L
16	H3D20065G	650	20	1.4	1.8	175	65	TO-263
17	H3D30065D	650	30	1.4	1.8	175	82	TO-247-3L
18	H3D40065D	650	40	1.4	1.8	175	112	TO-247-3L
19	H3D60065D	650	60	1.4	1.8	175	170	TO-247-3L
20	H3D60065H	650	60	1.4	1.8	175	170	TO-247-2L
21	H3D02120A	1200	2	1.4	2.0	175	11	TO-220-2L
22	H3D02120E	1200	2	1.4	2.0	175	11	TO-252-2L
23	H3D05120A	1200	5	1.5	2.0	175	24	TO-220-2L
24	H3D05120E	1200	5	1.5	2.0	175	24	TO-252-2L
25	H3D10120A	1200	10	1.5	2.2	175	50	TO-220-2L
26	H3D10120D	1200	10	1.5	2.2	175	48	TO-247-3L
27	H3D10120E	1200	10	1.5	2.2	175	50	TO-252-2L
28	H3D10120G	1200	10	1.5	2.2	175	50	TO-263
29	H3D10120H	1200	10	1.5	2.2	175	50	TO-247-2L
30	H3D15120G	1200	15	1.5	2.2	175	78	TO-263
31	H3D15120H	1200	15	1.5	2.2	175	78	TO-247-2L
32	H3D20120D	1200	20	1.5	2.2	175	100	TO-247-3L
33	H3D20120G	1200	20	1.5	2.2	175	95	TO-263
34	H3D20120H	1200	20	1.5	2.2	175	95	TO-247-2L
35	H3D30120D	1200	30	1.5	2.2	175	156	TO-247-3L
36	H3D40120D	1200	40	1.5	2.2	175	190	TO-247-3L
37	H3D40120H	1200	40	1.5	2.2	175	226	TO-247-2L
38	H3D12170H	1700	12	1.5	2.2	175	110	TO-247-2L
39	H3D20170H	1700	20	1.5	2.2	175	205	TO-247-2L
40	H4D10065A	650	10	1.4	1.8	175	20	TO-220-2L
41	H4D12065A	650	12	1.4	1.8	175	25	TO-220-2L



2. SiC MOSFET芯片选型表 (Bare Die)

序号	型号	击穿电压 (V)	导通电阻 (mΩ)	电流 (A)	芯片面积 (um*um)	芯片厚度 (um)	晶圆尺寸 (inch)	满版点数	包装	是否划片
1	GS2M-0650-0060	650	60	30	3300*3300	180	6	1410	蓝膜	是
2	GS2M-1200-0080	1200	80	20	3300*3300	180	6	1410	蓝膜	是
3	GS2M-1200-0160	1200	160	10	2390*2630	180	6	2380	蓝膜	是
4	GS2M-1700-0045	1700	45	40	TBD*	180	6	TBD*	蓝膜	是
5	GS2M-1700-1000	1700	1000	5	1610*1610	180	6	5700	蓝膜	是
6	GS2M-1700-050K	1700	50K	10m	TBD*	180	6	TBD*	蓝膜	是
7	GS3M-0650-0035	650	35	60	2880*4830	180	6	1100	蓝膜	是
8	GS3M-0650-0060	650	60	30	2880*2880	180	6	1820	蓝膜	是
9	GS3M-1200-0013A	1200	13	130	TBD*	180	6	TBD*	蓝膜	是
10	GS3M-1200-0018A	1200	18	100	TBD*	180	6	TBD*	蓝膜	是
11	GS3M-1200-0025	1200	25	80	TBD*	180	6	TBD*	蓝膜	是
12	GS3M-1200-0040	1200	40	60	2880*4830	180	6	1100	蓝膜	是
13	GS3M-1200-0080	1200	80	20	2880*2880	180	6	1820	蓝膜	是
14	GS3M-1200-0160	1200	160	10	TBD*	180	6	TBD*	蓝膜	是

*如需详细信息请联系销售

3. SiC MOSFET器件选型表 (Device)

序号	型号	击穿电压 (V)	导通电阻 (mΩ)	电流 (A)	阈值电压 (V)	最高工作结温 (°C)	封装形式
1	GS2M0060065D	650	60	30	2.4	175	TO-247-3L
2	GS2M0060065K	650	60	30	2.4	175	TO-247-4L
3	GS2M0060065G	650	60	30	2.4	175	TO-263-3L
4	GS2M0080120D	1200	80	20	2.4	175	TO-247-3L
5	GS2M0080120J	1200	80	20	2.4	175	TO-263-7L
6	GS2M0080120K	1200	80	20	2.4	175	TO-247-4L
7	GS2M0160120D	1200	160	10	2.4	175	TO-247-3L
8	GS2M0160120G	1200	160	10	2.4	175	TO-263-3L
9	GS2M0160120K	1200	160	10	2.4	175	TO-247-4L
10	GS2M0045170D	1700	45	40	2.4	175	TO-247-3L
11	GS2M1000170D	1700	1000	3.5	2.4	175	TO-247-3L
12	GS3M0035065K	650	35	60	3.0	175	TO-247-4L
13	GS3M0035065D	650	35	60	3.0	175	TO-247-3L
14	GS3M0025120D	1200	25	80	3.0	175	TO-247-3L
15	GS3M0025120K	1200	25	80	3.0	175	TO-247-4L
16	GS3M0040120D	1200	40	40	3.0	175	TO-247-3L
17	GS3M0040120K	1200	40	40	3.0	175	TO-247-4L